

# Bias Resistor Transistor

## PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

**LDTA143ELT1G**

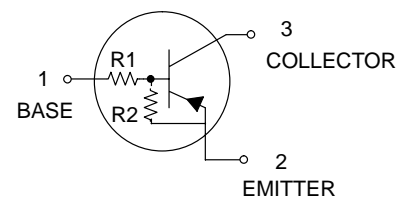
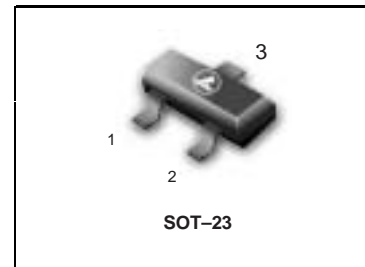
● **Applications**

Inverter, Interface, Driver

● **Features**

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on / off conditions need to be set for operation, making the device design easy.
- 4) Higher mounting densities can be achieved.

- We declare that the material of product compliance with RoHS requirements.



● **Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Supply voltage	V <sub>CC</sub>	-50	V
Input voltage	V <sub>IN</sub>	-30 to +10	V
Output current	I <sub>o</sub>	-100	mA
	I <sub>C(Max.)</sub>	-100	
Power dissipation	P <sub>D</sub>	200	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

**DEVICE MARKING AND RESISTOR VALUES**

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTA143ELT1G	A6J	4.7	4.7	3000/Tape & Reel
LDTA143ELT3G	A6J	4.7	4.7	10000/Tape & Reel

● **External characteristics (Unit: mm)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V <sub>I(off)</sub>	-	-	-0.5	V	V <sub>CC</sub> =-5V, I <sub>o</sub> =-100μA
	V <sub>I(on)</sub>	-3	-	-		V <sub>o</sub> =-0.3V, I <sub>o</sub> =-20mA
Output voltage	V <sub>O(on)</sub>	-	-0.1	-0.3	V	I <sub>o</sub> /I <sub>i</sub> =-10mA/-0.5mA
Input current	I <sub>i</sub>	-	-	-1.8	mA	V <sub>I</sub> =-5V
Output current	I <sub>o(off)</sub>	-	-	-0.5	μA	V <sub>CC</sub> =-50V, V <sub>I</sub> =0V
DC current gain	G <sub>I</sub>	30	-	-	-	V <sub>o</sub> =-5V, I <sub>o</sub> =-10mA
Input resistance	R <sub>1</sub>	3.29	4.7	6.11	kΩ	-
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	0.8	1	1.2	-	-
Transition frequency	f <sub>T</sub> *	-	250	-	MHz	V <sub>CE</sub> =-10V, I <sub>E</sub> =5mA, f=100MHz

\* Characteristics of built-in transistor

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● **Electrical characteristics curves**

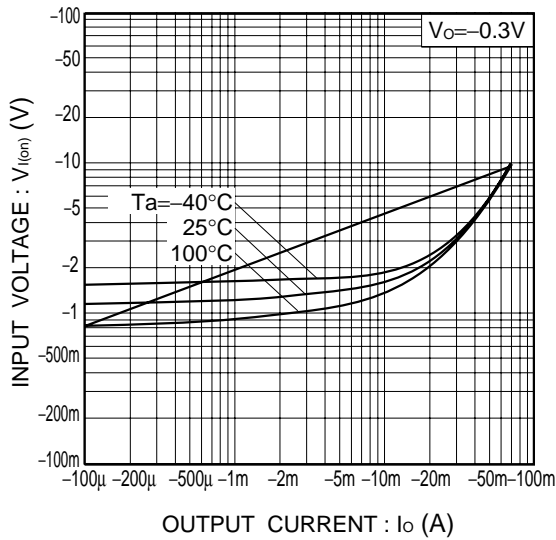


Fig.1 Input voltage vs. output current (ON characteristics)

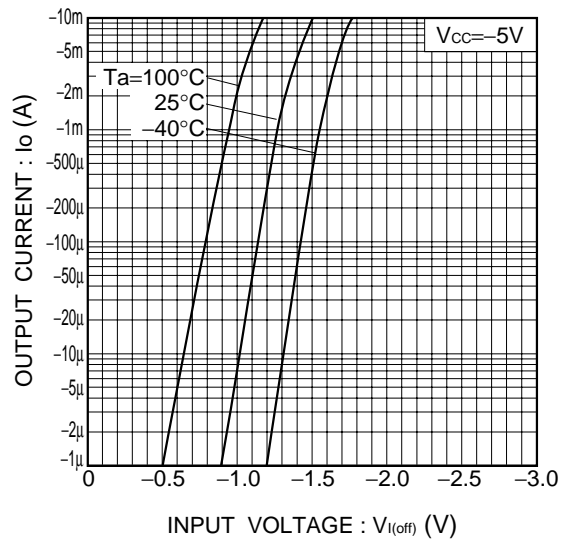


Fig.2 Output current vs. input voltage (OFF characteristics)

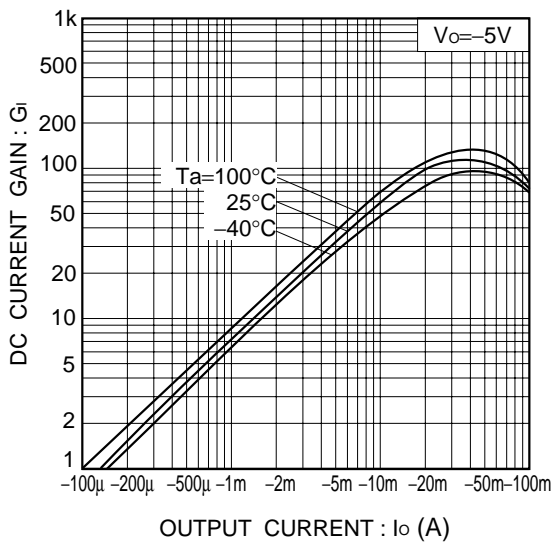


Fig.3 DC current gain vs. output current

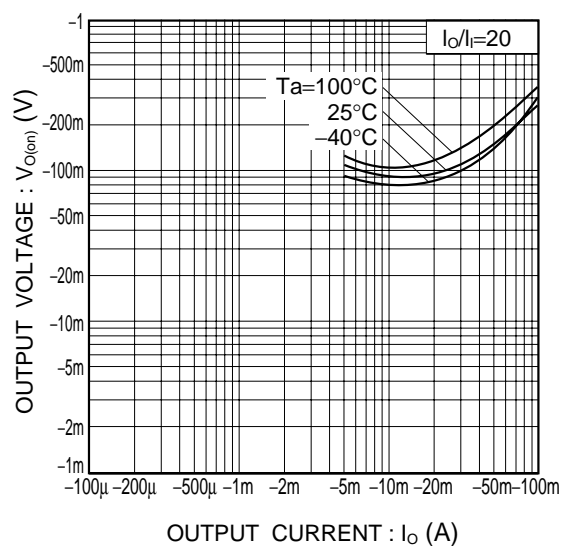


Fig.4 Output voltage vs. output current

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

